



Features:

Wide slot width: 0.375" (9.5 mm)Deep slot depth: 0.430" (10.9 mm)



Description:

The **OPB815** consists of an infrared Light Emitting Diode (LED) and an NPN silicon phototransistor mounted in a low-cost plastic housing. The device is designed to switch electrical states when an opaque object is passed through the slot. The slot is wider and deeper than many slotted switches and will accommodate a variety of different materials.

This device can be ordered with PCBoard solderable leads (OPB815L) or with 26 AWG stranded, UL rated wire length of 24" [610 mm] (OPB815WZ).

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Ordering Information									
Part	LED Peak		Slot	Aperture Emitter /Sensor	Lead Length /				
OPB815L	890 nm	Transistor	0.375" / 0.430"	None	0.10" / 0.53"				
OPB815WZ	890 nm	Transistor	0.375"/ 0.430"	None	24" / 26 AWG				

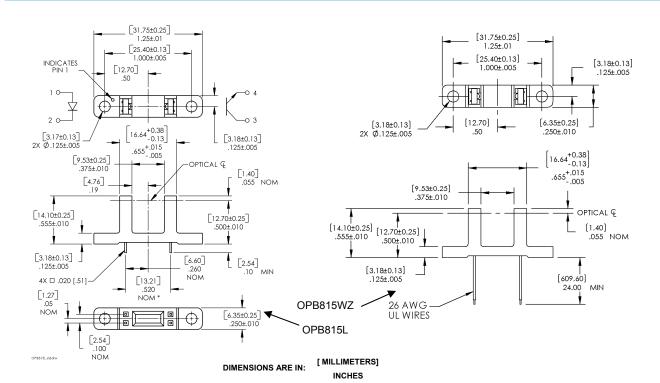
Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety





OPB815L, OPB815WZ Series



Pin#	Description			
1	Anode			
2	Cathode			
3	Collector			
4	Emitter			

Color	Description		
Red	Anode		
Black	Cathode		
White	Collector		
Green	Emitter		

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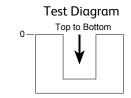
OPB815L, OPB815WZ Series

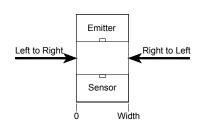
Electrical Specifications

			•					
Absolute	$\textbf{Maximum Ratings} \; (T_A \texttt{=} 25 ^{\circ} \text{C unless}$	otherw	ise not	ed)				
Storag	-40° C to +80° C							
Lead S	260° C							
Input Infro	red LED							
Contin	50 mA							
Reverse Voltage							2 V	
Power Dissipation ⁽²⁾							100 mW	
Output Pho	ototransistor							
Collector-Emitter Voltage							30 V	
Emitter-Collector Voltage							5 V	
Power Dissipation ⁽²⁾							100 mW	
Electrica	Characteristics (T _A = 25°C unless ot	herwise	noted	l)				
SYMBOL						CONDITIONS		
Input Infro	ared LED (see OP240 for additional inform	ation)			ı			
V _F	Forward Voltage	-	-	1.7	V	I _F = 20 mA		
I_{R}	Reverse Current		-	100	μA	V _R = 2 V		
Output Pho	ototransistor (see OP550 for additional inf	ormatio	n)					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _C = 1 mA		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	v	Ι _ε = 100 μΑ		
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 10 V, I _F = 0, E _E = 0		
Coupled	1	1	ı	ı	I	1		
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.4	V	I _C = 500 μA, I _F = 20 mA		
$I_{C(ON)}$	On-State Collector Current	3.5	-	16	mA	V _{CE} = 10 V, I _F = 20 mA		

Notes:

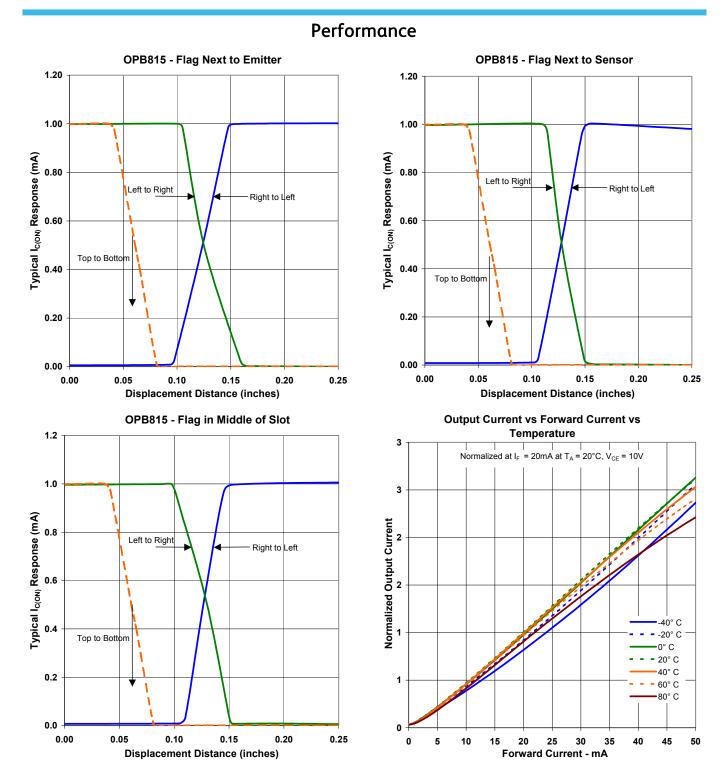
- (1) All wires are 26 AWG stranded, UL rated.
- (2) Derate linearly 1.67mW/°C above 25° C.
- (3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.
- (4) All parameters tested using pulse techniques.







OPB815L, OPB815WZ Series



Refer to Test Diagram on page 2 for definition of "Top to Bottom", "Left to Right" and "Right to Left"